Ordering number : ENA1458A

SANYO Semiconductors
DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

ATP405 — General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS}(on)$=25mΩ (typ.)
- 10V drive
- Input capacitance Ciss=4000pF (typ.)
- Halogen free compliance

Specifications

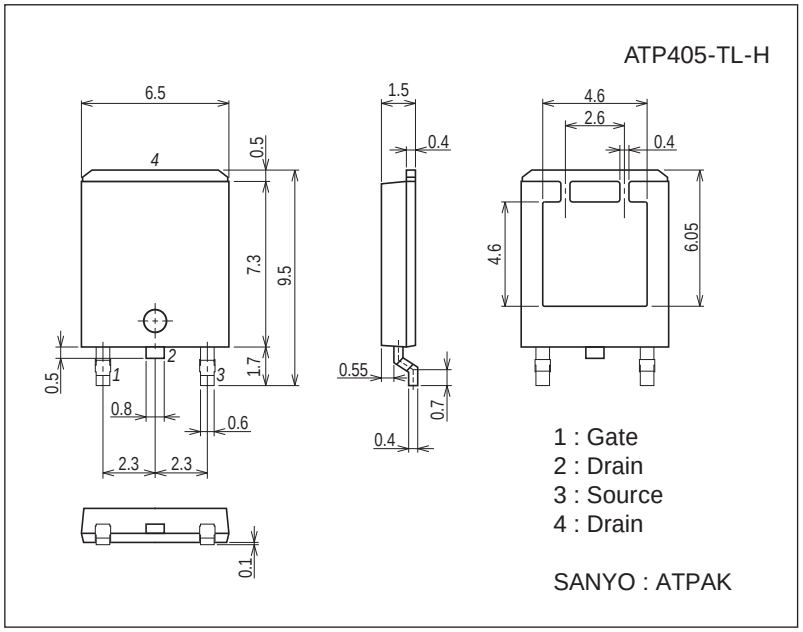
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		100	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		40	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	160	A
Allowable Power Dissipation	P_D	Tc=25°C	70	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C
Avalanche Energy (Single Pulse) *1	E_{AS}		148	mJ
Avalanche Current *2	I_{AV}		40	A

Note :*1 V_{DD}=30V, L=100μH, I_{AV}=40A
*2 L≤100μH, Single pulse

Package Dimensions

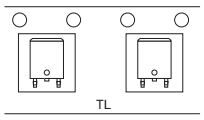
unit : mm (typ)
7057-001



Product & Package Information

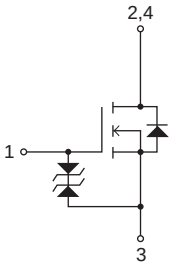
- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

Packing Type: TL



Marking

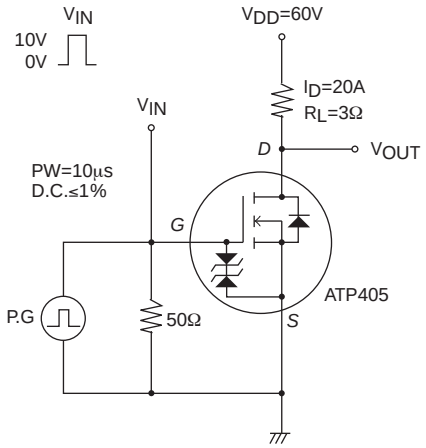
Electrical Connection



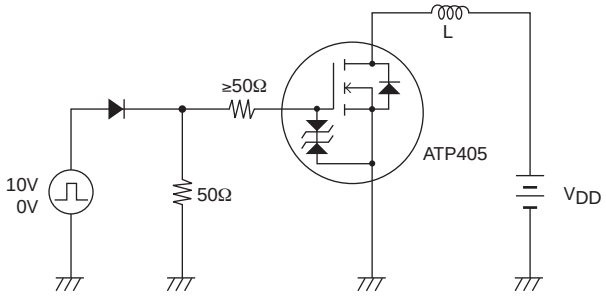
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	100			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V			10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	2.0		3.5	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=20A		62		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)	I_D=20A, V_{GS}=10V		25	33	mΩ
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		4000		pF
Output Capacitance	Coss			300		pF
Reverse Transfer Capacitance	Crss			170		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		38		ns
Rise Time	t_r			125		ns
Turn-OFF Delay Time	t_d(off)			220		ns
Fall Time	t_f			150		ns
Total Gate Charge	Qg	V_{DS}=60V, V_{GS}=10V, I_D=40A		68		nC
Gate-to-Source Charge	Qgs			14		nC
Gate-to-Drain “Miller” Charge	Qgd			15		nC
Diode Forward Voltage	V_{SD}	I_S=40A, V_{GS}=0V		0.9	1.2	V

Switching Time Test Circuit

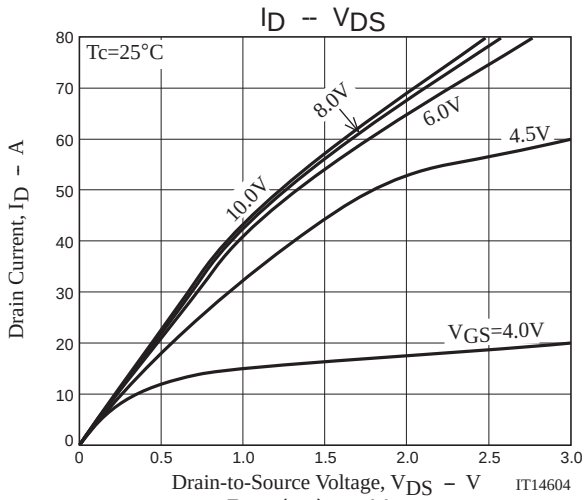


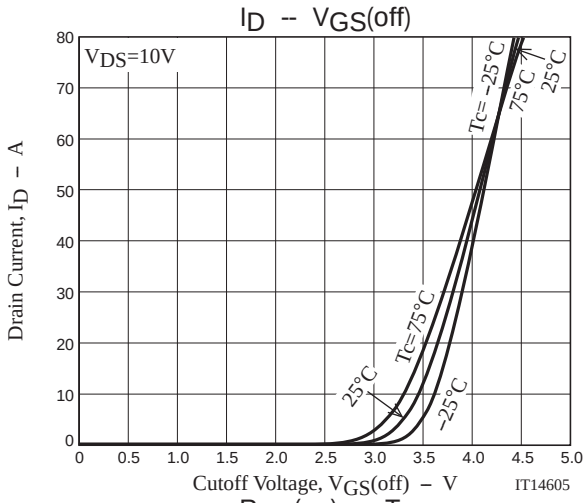
Avalanche Resistance Test Circuit

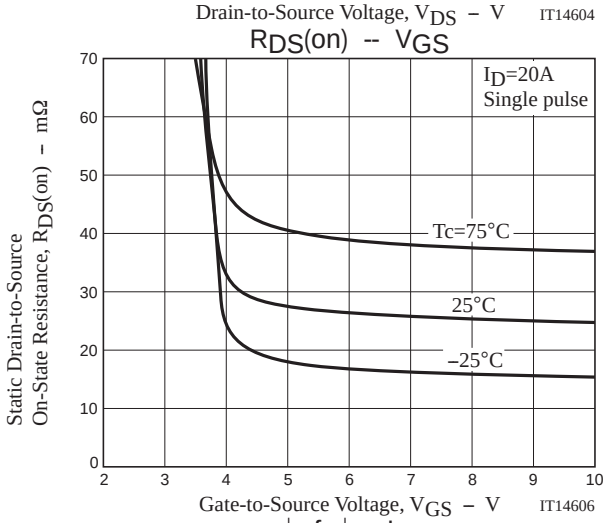


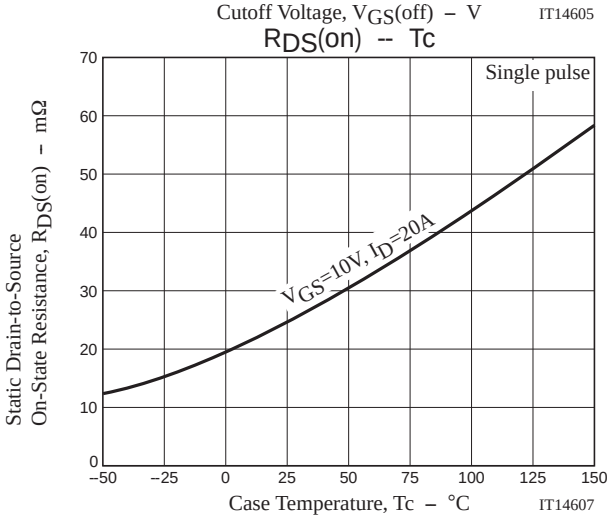
Ordering Information

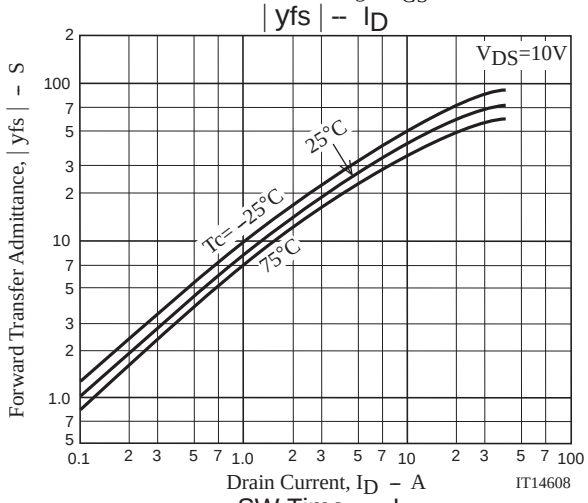
Device	Package	Shipping	memo
ATP405-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free

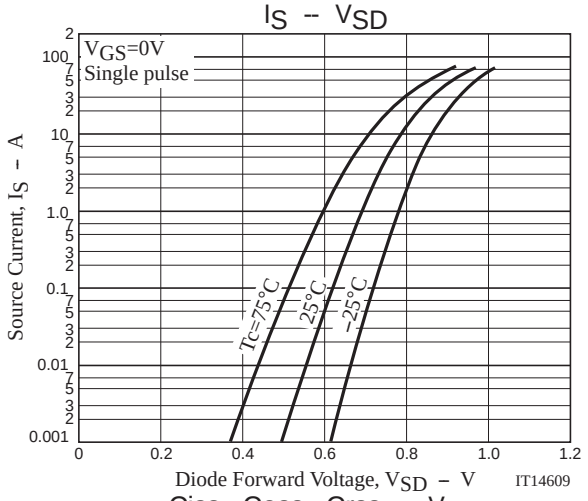

ID -- VDS
Tc=25°C
8.0V
6.0V
4.5V
10.0V
VGS=4.0V
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT14604

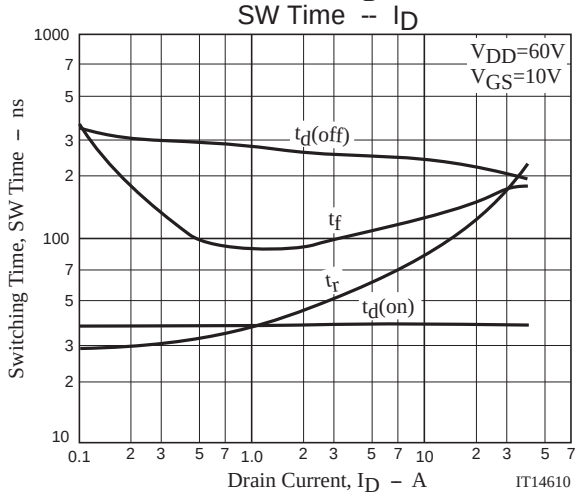

ID -- VGS(off)
VDS=10V
Tc= –25°C
75°C
25°C
Tc=75°C
25°C
–25°C
Drain Current, ID – A
Cutoff Voltage, VGS(off) – V
IT14605

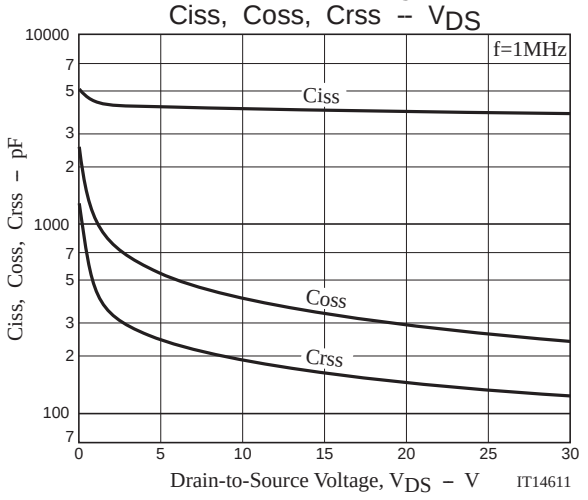

RDS(on) -- VGS
ID=20A
Single pulse
Tc=75°C
25°C
–25°C
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V
IT14606

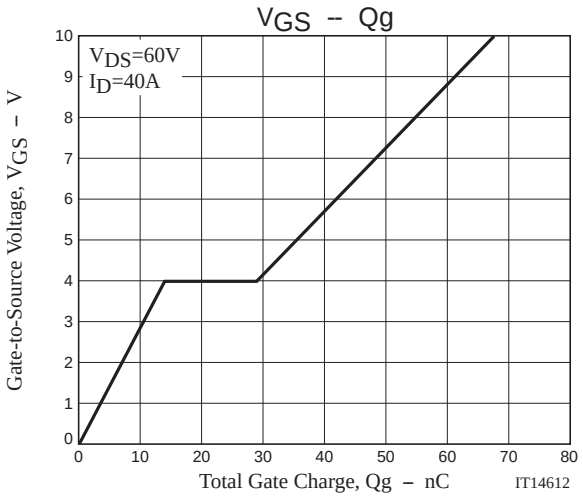

RDS(on) -- Tc
Single pulse
VGS=10V, ID=20A
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Case Temperature, Tc – °C
IT14607

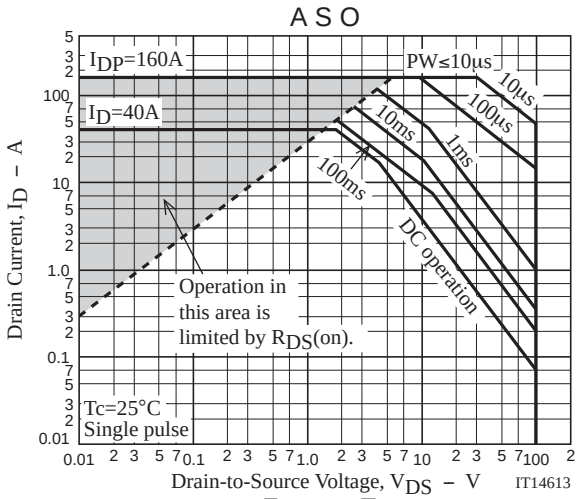

| yfs | -- ID
VDS=10V
25°C
Tc= –25°C
75°C
Forward Transfer Admittance, | yfs | – S
Drain Current, ID – A
IT14608

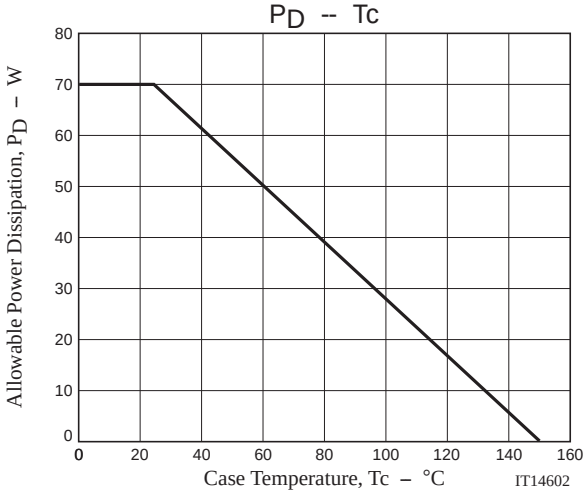

IS -- VSD
VGS=0V
Single pulse
Tc=75°C
25°C
–25°C
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT14609

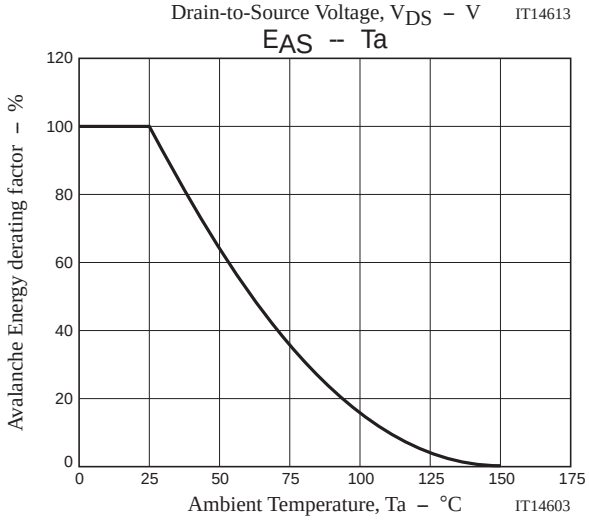

SW Time -- ID
VDD=60V
VGS=10V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT14610


Ciss, Coss, Crss -- VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT14611


VGS – Qg
VDS=60V
ID=40A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT14612


A S O
IDP=160A
ID=40A
PW≤10μs
10μs
100μs
10ms
1ms
100ms
DC operation
Operation in this area is limited by RDS(on).
Tc=25°C
Single pulse
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT14613


PD -- Tc
Allowable Power Dissipation, PD – W
Case Temperature, Tc – °C
IT14602


EAS -- Ta
Avalanche Energy derating factor – %
Ambient Temperature, Ta – °C
IT14603

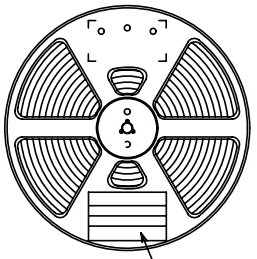
Taping Specification

ATP405-TL-H

1. Packing Format (TL)

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
ATPAK	ATP	3,000	3,000	15,000	1 reels contained Dimensions:mm (external) 340×340×28	5 inner boxes contained Dimensions:mm (external) 355×355×165

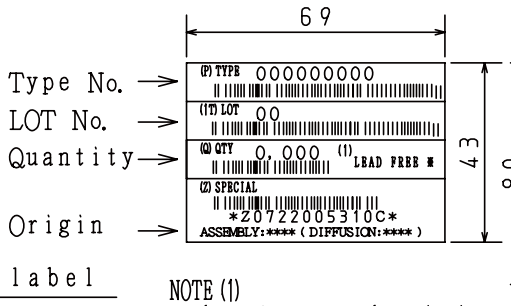
Packing method



Reel label

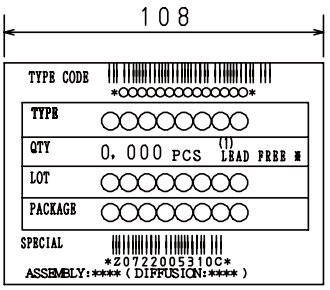
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



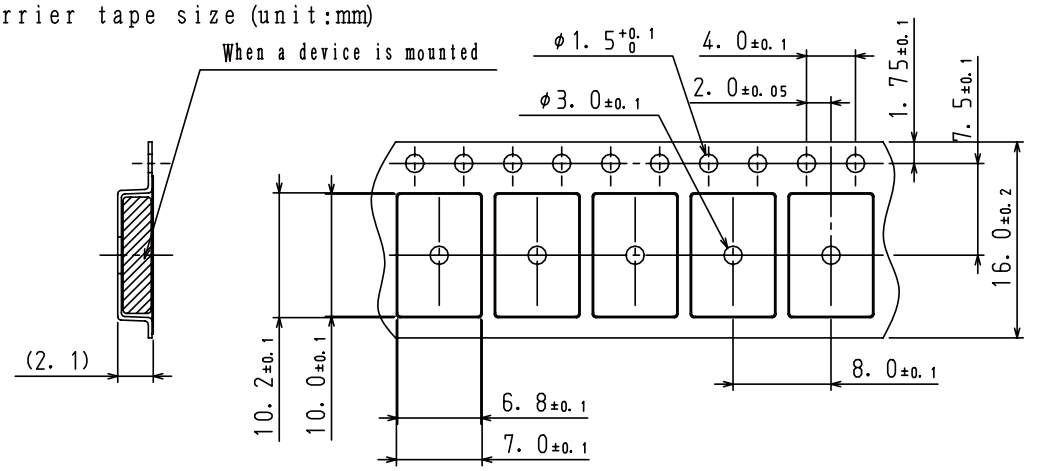
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

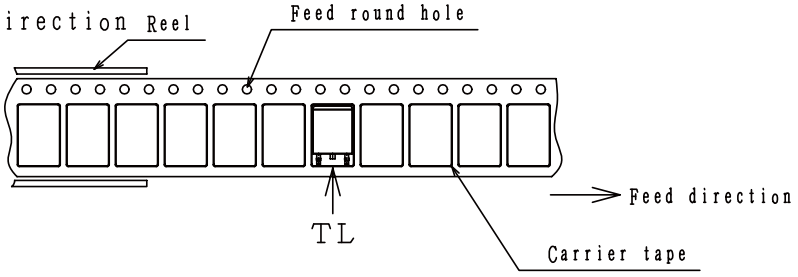
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



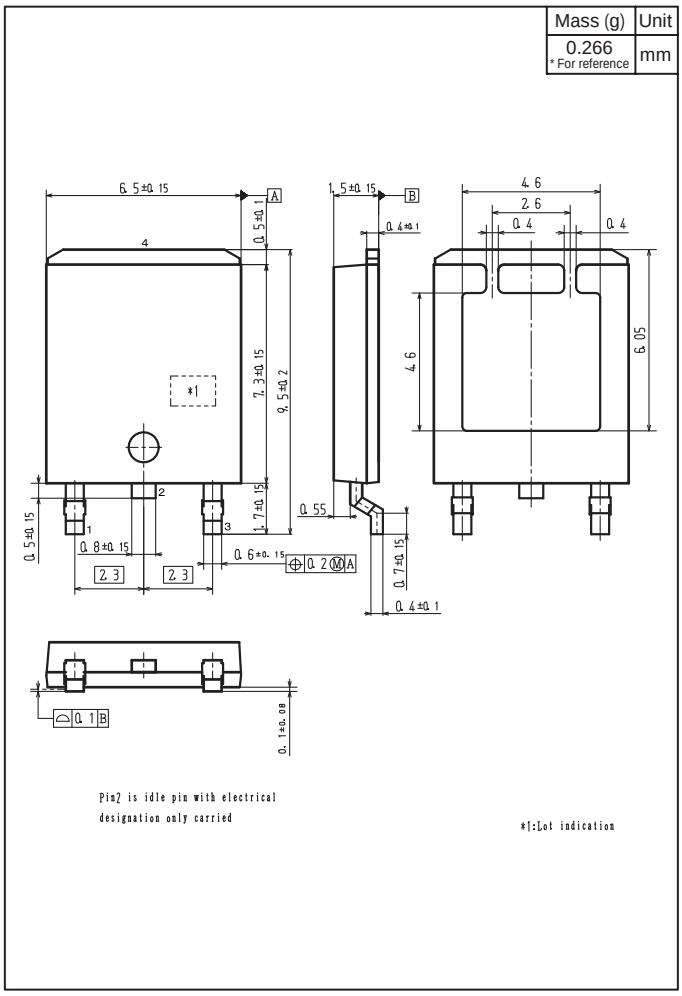
2-2. Device placement direction



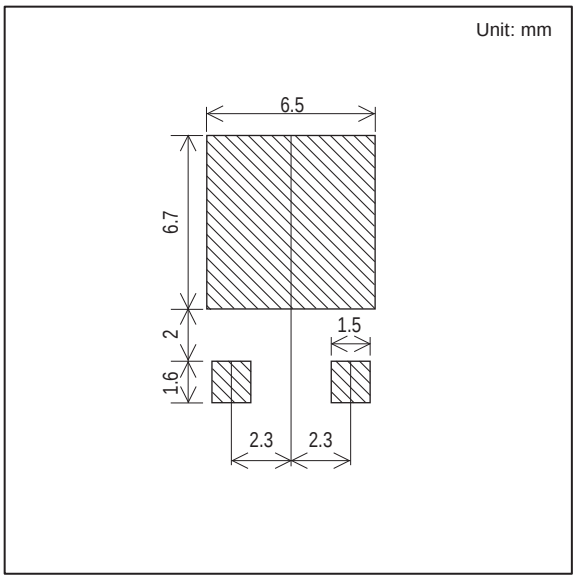
The one erectrode terminals on feed hole side····TL

Outline Drawing

ATP405-TL-H



Land Pattern Example



Note on usage : Since the ATP405 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

This catalog provides information as of June, 2012. Specifications and information herein are subject to change without notice.